



# Wireless Components

ASK Single Conversion Receiver TDA 5201 Version 1.4

Specification March 2000

tory	
on: 1.4 as of 07	7.03.00
ion: 1.3, Nov. 1	999
Page (in current Version)	Subjects (major changes since last revision)
	on: 1.4 as of 07 ion: 1.3, Nov. 1 Page (in current

ABM®, AOP®, ARCOFI®, BA, ARCOFI®-BA, ARCOFI®-SP, DigiTape®, EPIC®-1, EPIC®-S, ELIC®, FALC®54, FALC®56, FALC®-E1, FALC®-LH, IDEC®, IOM®, IOM®-1, IOM®-2, IPAT®-2, ISAC®-P, ISAC®-S, ISAC®-S TE, ISAC®-P TE, ITAC®, IWE®, MUSAC®-A, OCTAT®-P, QUAT®-S, SICAT®, SICOFI®, SICOFI®-2, SICOFI®-4, SICOFI®-4µC, SLICOFI® are registered trademarks of Infineon Technologies AG.

ACE™, ASM™, ASP™, POTSWIRE™, QuadFALC™, SCOUT™ are trademarks of Infineon Technologies AG.

Edition 03.00 Published by Infineon Technologies AG, Balanstraße 73, 81541 München

© Infineon Technologies AG March 2000. All Rights Reserved.

#### Attention please!

As far as patents or other rights of third parties are concerned, liability is only assumed for components, not for applications, processes and circuits implemented within components or assemblies.

The information describes the type of component and shall not be considered as assured characteristics.

Terms of delivery and rights to change design reserved.

Due to technical requirements components may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies Office.

Infineon Technologies AG is an approved CECC manufacturer.

#### **Packing**

Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport.

For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

#### Components used in life-support devices or systems must be expressly authorized for such purpose!

Critical components<sup>1</sup> of the Infineon Technologies AG, may only be used in life-support devices or systems<sup>2</sup> with the express written approval of the Infineon Technologies AG.

- 1 A critical component is a component used in a life-support device or system whose failure can reasonably be expected to cause the failure of that life-support device or system, or to affect its safety or effectiveness of that device or system.
- 2 Life support devices or systems are intended (a) to be implanted in the human body, or (b) to support and/or maintain and sustain human life. If they fail, it is reasonable to assume that the health of the user may be endangered.

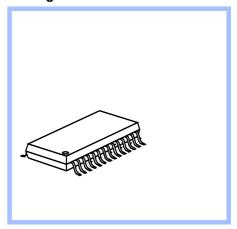
**Product Info** 

#### **Product Info**

#### **General Description**

The IC is a very low power consumption single chip ASK Single Conversion Receiver for receive frequencies between 310 and 345MHz. The Receiver offers a high level of integration and needs only a few external components. The device contains a low noise amplifier (LNA), a double balanced mixer, a fully integrated VCO, a PLL synthesiser, a crystal oscillator, a limiter with RSSI generator, a data filter, a data comparator (slicer) and a peak detector. Additionally there is a power down feature to save battery life.

#### **Package**



#### **Features**

- Low supply current (I<sub>s</sub> = 4.6mA typ.)
- Supply voltage range 5V ±10%
- Power down mode with very low supply current (50nA typ)
- Fully integrated VCO and PLL Synthesiser
- RF input sensitivity < -110dBm

- Selectable frequency ranges 308-312 MHz and 343-347 MHz
- Selectable reference frequency
- Limiter with RSSI generation, operating at 10.7MHz
- 2nd order low pass data filter with external capacitors
- Data slicer with self-adjusting threshold

#### **Application**

- Keyless Entry Systems
- Remote Control Systems
- Fire Alarm Systems
- Low Bitrate Communication Systems

#### **Ordering Information**

Туре	Ordering Code	Package
TDA 5201	Q67037-A1118	P-TSSOP-28-1
available on tape and reel		

1	Table	of Contents	
2	Produ	ıct Description	2-1
	2.1	Overview	2-2
	2.2	Application	2-2
	2.3	Features	2-2
	2.4	Package Outlines	2-3
3	Funct	ional Description	3-1
	3.1	Pin Configuration	3-2
	3.2	Pin Definition and Function	3-3
	3.3	Functional Block Diagram	3-9
	3.4	Functional Blocks	3-10
	3.4.1	Low Noise Amplifier (LNA)	3-10
	3.4.2	Mixer	3-10
	3.4.3	PLL Synthesizer	3-10
	3.4.4	Crystal Oscillator	3-11
	3.4.5	Limiter	3-11
	3.4.6	Data Filter	3-11
	3.4.7	Data Slicer	3-11
	3.4.8	Peak Detector	3-12
	3.4.9	Bandgap Reference Circuitry	3-12
4	Appli	cations	4-1
	11	Chaiga of LNA Throchold Voltage and Time Constant	4.0

	4.2	Data Filter Design	4-4
	4.3	Quartz Load Capacitance Calculation	4-5
	4.4	Quartz Frequency Calculation	4-6
	4.5	Data Slicer Threshold Generation	4-7
5	Refer	ence	5-1
	5.1	Electrical Data	5-2
	5.1.1	Absolute Maximum Ratings	5-2
	5.1.2	Operating Range	5-3
	5.1.3	AC/DC Characteristics	5-4
	5.2	Test Circuit	5-8
	5.3	Test Board Layouts	5-9
	5.4	Bill of Materials	5-11
	5.5	Appendix - Noise Figure and Gain Circles	5-13

# Product Description

2.3

2.4

# 2.1 Overview. 2-2 2.2 Application 2-2



#### 2.1 Overview

The IC is a very low power consumption single chip ASK Superheterodyne Receiver (SHR) for the frequency bands 315 and 345MHz. The SHR offers a high level of integration and needs only a few external components. The device contains a low noise amplifier (LNA), a double balanced mixer, a fully integrated VCO, a PLL synthesiser, a crystal oscillator, a limiter with RSSI generator, a data filter, a data comparator (slicer) and a peak detector. Additionally there is a power down feature to save battery life.

### 2.2 Application

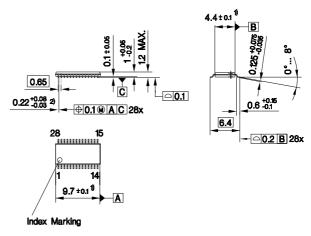
- Keyless Entry Systems
- Remote Control Systems
- Fire Alarm Systems
- Low Bitrate Communication Systems

#### 2.3 Features

- Low supply current (Is = 4.6mA typ.)
- Supply voltage range 5V ±10%
- Power down mode with very low supply current (50nA typ.)
- Fully integrated VCO and PLL Synthesiser
- RF input sensitivity < -110dBm
- Selectable receive frequency bands 315 and 345MHz
- Selectable reference frequency
- Limiter with RSSI generation, operating at 10.7MHz
- 2nd order low pass data filter with external capacitors
- Data slicer with self-adjusting threshold



# 2.4 Package Outlines



- 1) Does not include plastic or metal protrusion of 0.15 max. per side
- 2) Does not include dambar protrusion

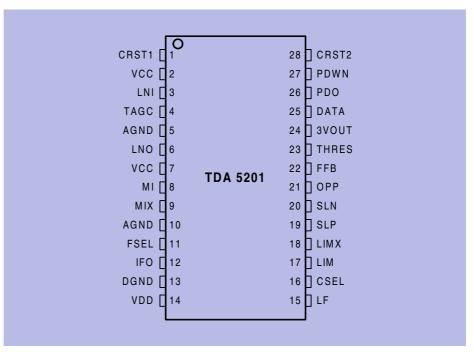
P\_TSSOP\_28.EPS

Figure 2-1 P-TSSOP-28-1 package outlines

Con	Contents of this Chapter				
3.1	Pin Configuration	. 3-2			
3.2	Pin Definition and Function	. 3-3			
3.3	Functional Block Diagram	. 3-9			
3.4	Functional Blocks	3-10			



# 3.1 Pin Configuration



Pin\_Configuration\_5201\_V1.4.wmf

Figure 3-1 IC Pin Configuration



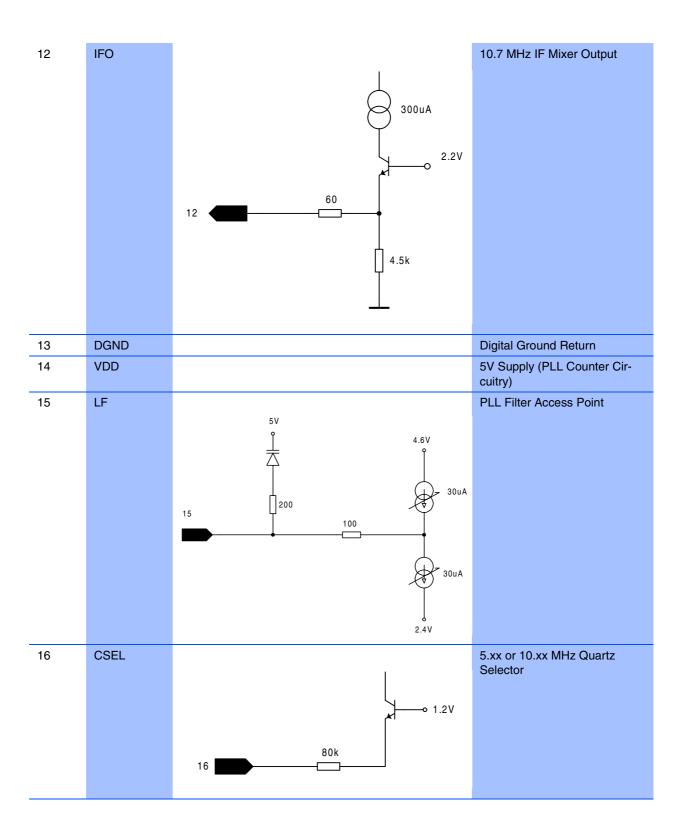
### 3.2 Pin Definition and Function

Table 3-	l Pin Definition	and Function	
Pin No.	Symbol	Equivalent I/O-Schematic	Function
1	CRST1	4.15V 50uA	External Crystal Connector 1
2	VCC		5V Supply
3	LNI	57uA 3 500uA	LNA Input

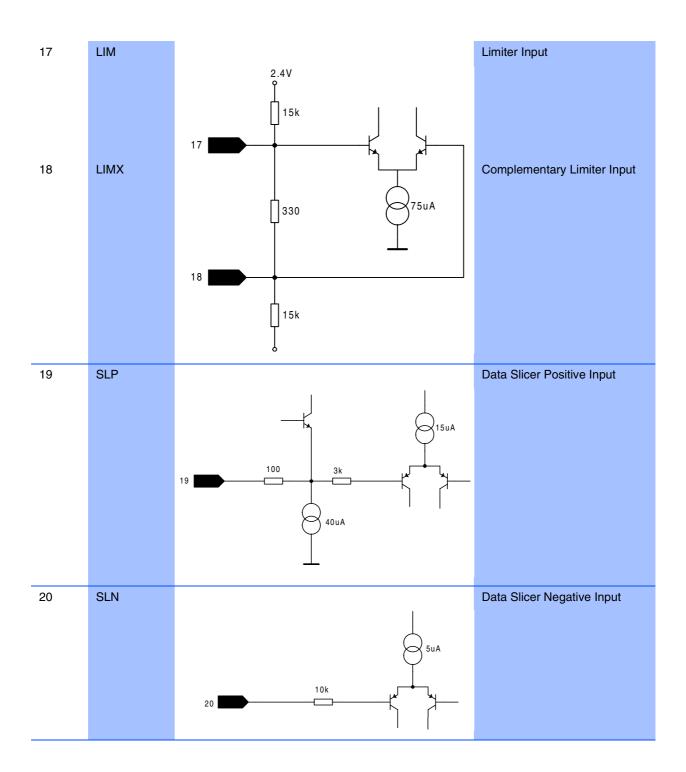


4	TAGC	4.3V 3uA 1k 1.4uA	AGC Time Constant Control
5	AGND		Analogue Ground Return
6	LNO		LNA Output
		5V	
7	VCC		5V Supply
9	MIX	1.7V 2k 2k 400uA	Mixer Input  Complementary Mixer Input
10	AGND		Analogue Ground Return
11	FSEL		not applicable - has to be left open











21	OPP	5uA	OpAmp Noninverting Input
		21	
22	FFB	5uA	Data Filter Feedback Pin
		22 100k	
23	THRES	5uA	AGC Threshold Input
		23 10k	
24	3VOUT	24	3V Reference Output
		3V	
25	DATA		Data Output
		25 ————————————————————————————————————	



26	PDO	26	Peak Detector Output
27	PDWN	220k	Power Down Input
28	CRST2	4.15V 50uA	External Crystal Connector 2



# 3.3 Functional Block Diagram

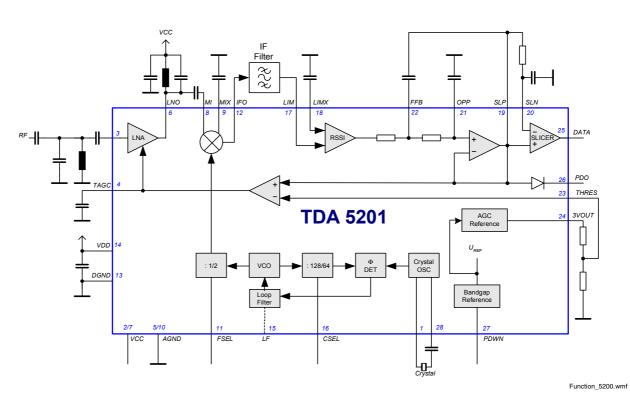


Figure 3-2 Main Block Diagram



#### 3.4 Functional Blocks

#### 3.4.1 Low Noise Amplifier (LNA)

The LNA is an on-chip cascode amplifier with a voltage gain of 15 to 20dB. The gain figure is determined by the external matching networks situated ahead of LNA and between the LNA output LNO (Pin 6) and the Mixer Inputs MI and MIX (Pins 8 and 9). The noise figure of the LNA is approximately 2dB, the current consumption is 500µA. The gain can be reduced by approximately 18dB. The switching point of this AGC action can be determined externally by applying a threshold voltage at the THRES pin (Pin 23). This voltage is compared internally with the received signal (RSSI) level generated by the limiter circuitry. In case that the RSSI level is higher than the threshold voltage the LNA gain is reduced and vice versa. The threshold voltage can be generated by attaching a voltage divider between the **3VOUT** pin (Pin 24) which provides a temperature stable 3V output generated from the internal bandgap voltage and the **THRES** pin as described in Section 4.1. The time constant of the AGC action can be determined by connecting a capacitor to the TAGC pin (Pin 4) and should be chosen along with the appropriate threshold voltage according to the intended operating case and interference scenario to be expected during operation. The optimum choice of AGC time constant and the threshold voltage is described in Section 4.1.

#### 3.4.2 Mixer

The Double Balanced Mixer downconverts the input frequency (RF) in the range of 310 or 345MHz to the intermediate frequency (IF) at 10.7MHz with a voltage gain of approximately 21dB. A low pass filter with a corner frequency of 20MHz is built on chip in order to suppress RF signals to appear at the IF output (  $\mbox{\bf IFO}$  pin). The IF output is internally consisting of an emitter follower that has a source impedance of approximately 330  $\Omega$  to facilitate interfacing the pin directly to a standard 10.7MHz ceramic filter without additional matching circuitry.

#### 3.4.3 PLL Synthesizer

The Phase Locked Loop synthesiser consists of a VCO, an asynchronous divider chain, a phase detector with charge pump and a loop filter and is fully implemented on-chip. The VCO is including spiral inductors and varactor diodes. It's nominal centre frequency is 660MHz. The FSEL pin (Pin 11) has to be left open. No additional components are necessary. The oscillator signal is fed both to the synthesiser divider chain and to the downconverting mixer. The VCO signal is divided by two before it is fed to the mixer. The loop filter is also realised fully on-chip.



#### 3.4.4 Crystal Oscillator

The on-chip crystal oscillator circuitry allows for utilisation of quartzes both in the 5 and 10MHz range as the overall division ratio of the PLL can be switched between 64 and 128 via the **CSEL** (Pin 16) pin according to the following table.

Table 3-2 CSEL Pin Operating States	
CSEL	Crystal Frequency
Open	5.xx MHz
Shorted to ground	10.xx MHz

The calculation of the value of the necessary quartz load capacitance is shown in Section 4.3, the quartz frequency calculation is expained in Section 4.4.

#### 3.4.5 Limiter

The Limiter is an AC coupled multistage amplifier with a cumulative gain of approximately 80dB that has a bandpass-characteristic centred around 10.7MHz. It has an input impedance of 330  $\Omega$  to allow for easy interfacing to a 10.7MHz ceramic IF filter. The limiter circuit acts as a Receive Signal Strength Indicator (RSSI) generator which produces a DC voltage that is directly proportional to the input signal level as can be seen in Figure 4-2. This signal is used to demodulate the ASK receive signal in the subsequent baseband circuitry and to turn down the LNA gain by approximately 18dB in case the input signal strength is too strong as described in Section 3.4.1 and Section 4.1.

#### 3.4.6 Data Filter

The data filter comprises an OP-Amp with a bandwidth of 100kHz used as a voltage follower and two  $100k\Omega$  on-chip resistors. Along with two external capacitors a 2nd order Sallen-Key low pass filter is formed. The selection of the capacitor values is described in Section 4.2.

#### 3.4.7 Data Slicer

The data slicer is a fast comparator with a bandwidth of 100 kHz. This allows for a maximum receive data rate of approximately 120kBaud. The maximum achievable data rate also depends on the IF Filter bandwidth and the local oscillator tolerance values. Both inputs are accessible. The output delivers a digital data signal (CMOS-like levels) for the detector. The self-adjusting threshold on pin 20 its generated by RC-term or peak detector depending on the baseband coding scheme. The data slicer threshold generation alternatives are described in more detail in Section 4.5.



#### 3.4.8 Peak Detector

The peak detector generates a DC voltage which is proportional to the peak value of the receive data signal. An external RC network is necessary. The output can be used as an indicator for the signal strength and also as a reference for the data slicer. The maximum output current is  $500\mu A$ .

#### 3.4.9 Bandgap Reference Circuitry

A Bandgap Reference Circuit provides a temperature stable reference voltage for the device. A power down mode is available to switch off all subcircuits which is controlled by the PWDN pin (Pin 27) as shown in the following table. The supply current drawn in this case is typically 50nA.

Table 3-3 PDWN Pin Operating States	
PDWN	Operating State
Open or tied to ground	Powerdown Mode
Tied to Vs	Receiver On

# 4 Applications

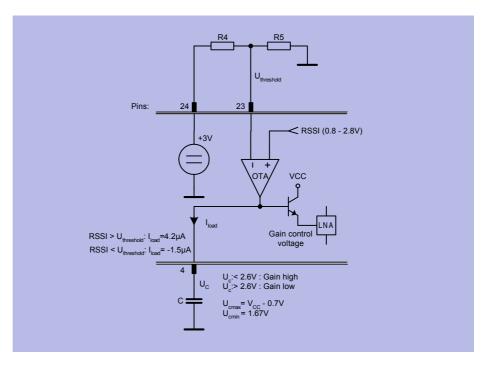
#### **Contents of this Chapter**

4.1	Choice of LNA Threshold Voltage and Time Constant	4-2
4.2	Data Filter Design	4-4
4.3	Quartz Load Capacitance Calculation	4-5
4.4	Quartz Frequency Calculation	4-6
4.5	Data Slicer Threshold Generation	4-7



#### 4.1 Choice of LNA Threshold Voltage and Time Constant

In the following figure the internal circuitry of the LNA automatic gain control is shown.



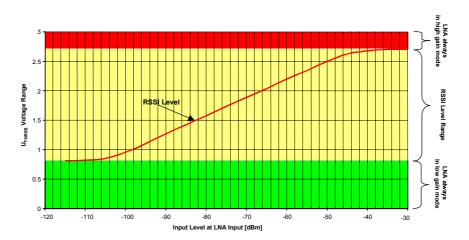
LNA\_autom.wmf

Figure 4-1 LNA Automatic Gain Control Circuitry

The LNA automatic gain control circuitry consists of an operational transimpedance amplifier that is used to compare the received signal strength signal (RSSI) generated by the Limiter with an externally provided threshold voltage  $U_{thres}$ . As shown in the following figure the threshold voltage can have any value between approximately 0.8 and 2.8V to provide a switching point within the receive signal dynamic range.

This voltage  $U_{thres}$  is applied to the **THRES** pin (Pin 23) The threshold voltage can be generated by attaching a voltage divider between the **3VOUT** pin (Pin 24) which provides a temperature stable 3V output generated from the internal bandgap voltage and the **THRES** pin. If the RSSI level generated by the Limiter is higher than  $U_{thres}$ , the OTA generates a positive current  $I_{load}$ . This yields a voltage rise on the **TAGC** pin (Pin 4). Otherwise, the OTA generates a negative current. These currents do not have the same values in order to achieve a fast-attack and slow-release action of the AGC and are used to charge an external capacitor which finally generates the LNA gain control voltage.





RSSI-AGC.wmf

Figure 4-2 RSSI Level and Permissive AGC Threshold Levels

The switching point should be chosen according to the intended operating scenario. The determination of the optimum point is described in the accompanying Application Note, a threshold voltage level of 1.8V is apparently a viable choice. It should be noted that the output of the 3VOUT pin is capable of driving up to 50µA, but that the THRES pin input current is only in the region of 40nA. As the current drawn out of the 3VOUT pin is directly related to the receiver power consumption, the power divider resistors should have high impedance values. R4 can be chosen as  $120k\Omega$ , R5 as  $180k\Omega$  to yield an overall 3VOUT output current of  $10\mu$ A.

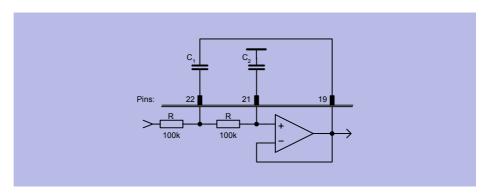
**Note:** If the LNA gain shall be kept in either high or low gain mode this has to be accomplished by tying the **THRES** pin to a fixed voltage. In order to achieve high gain mode operation, a voltage higher than 2.8V shall be applied to the **THRES** pin, such as a short to the **3VOLT** pin. In order to achieve low gain mode operation a voltage lower than 0.7V shall be applied to the **THRES**, such as a short to ground.

As stated above the capacitor connected to the **TAGC** pin is generating the gain control voltage of the LNA due to the charging and discharging currents of the OTA and thus is also responsible for the AGC time constant. As the charging and discharging currents are not equal two different time constants will result. The time constant corresponding to the charging process of the capacitor shall be chosen according to the data rate. According to measurements performed at Infineon the capacitor value should be greater than 47nF.

**Applications** 

#### 4.2 Data Filter Design

Utilising the on-board voltage follower and the two  $100k\Omega$  on-chip resistors a 2nd order Sallen-Key low pass data filter can be constructed by adding 2 external capacitors between pins 19 (SLP) and 22 (FFB) and to pin 21 (OPP) as depicted in the following figure and described in the following formulas  $^1$ .



Filter Design.wmf

Figure 4-3 Data Filter Design

$$C1 = \frac{2Q\sqrt{b}}{R2\Pi f_{3dB}} \qquad C2 = \frac{\sqrt{b}}{4QR\Pi f_{3dB}}$$

with

$$Q = \frac{\sqrt{b}}{a}$$

(3) the quality factor of the poles

where

in case of a Bessel filter a = 1.3617, b = 0.618

and thus Q = 0.577

and in case of a Butterworth filter a = 1.141, b = 1

and thus Q = 0.71

Example: Butterworth filter with  $f_{3dB} = 5kHz$  and  $R = 100k\Omega$ :

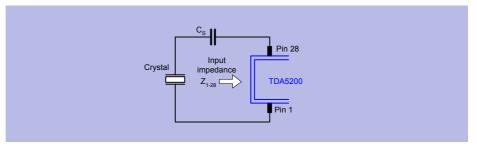
$$C_1 = 450pF, C_2 = 225pF$$

1. taken from Tietze/Schenk: Halbleiterschaltungstechnik, Springer Berlin, 1999

**Applications** 

#### 4.3 Quartz Load Capacitance Calculation

The value of the capacitor necessary to achieve that the quartz oscillator is operating at the intended frequency is determined by the reactive part of the negative resistance of the oscillator circuit as shown in Section 5.1.3 and by the quartz specifications given by the quartz manufacturer.



Quartz load wmf

Figure 4-4 Determination of Series Capacitance Value for the Quartz Oscillator

Crystal specified with load capacitance

$$C_S = \frac{1}{\frac{1}{C_I} + 2\pi f X_L}$$

with C<sub>I</sub> the load capacitance (refer to the quartz crystal specification).

#### Examples:

These values may be obtained by putting two capacitors in series to the quartz, such as 18pF and 22pF in the 5.1MHz case and 18pF and 12pF in the 10.2MHz case.



#### 4.4 Quartz Frequency Calculation

The quartz frequency is calculated by using the following formula:

$$f_{QU} = (f_{RF} \pm 10.7) / r$$
 (1),

with  $f_{RF}$  .... receive frequency

 $f_{LO}$  .... local oscillator (PLL) frequency ( $f_{RF} \pm 10.7$ )

 $f_{\rm QU}$  .... quartz oscillator frequency

r .... ratio of local oscillator (PLL) frequency and quartz

frequency as shown in the subsequent table.

Table 4-1 PLL Division Ratio Dependence on States of CSEL					
CSEL	Ratio r = (f <sub>LO</sub> /f <sub>QU</sub> )				
open	64				
GND	32				

Addition of 10.7 is used in case of operation the device at 315 MHz, subtraction in case of operation at 345 MHz. This yields the following frequencies:

CSEL tied to GND:

$$f_{\rm QU} = (315\,MHz + 10.7\,MHz)/32 = 10.1781\,MHz$$

$$f_{\text{QU}} = (345 \, MHz - 10.7 \, MHz) / 32 = 10.4469 \, MHz$$

CSEL open:

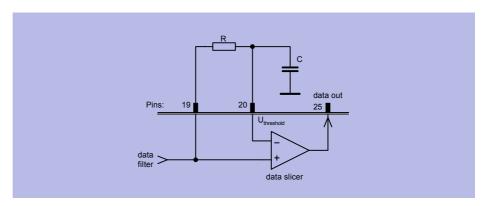
$$f_{\text{QU}} = (315 \, MHz + 10.7 \, MHz) / 64 = 5.0891 \, MHz$$

$$f_{\text{QU}} = (345 \, MHz - 10.7 \, MHz) / 64 = 5.2234 \, MHz$$



#### 4.5 Data Slicer Threshold Generation

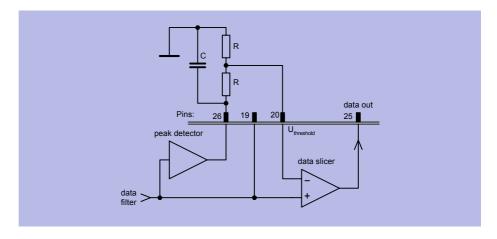
The threshold of the data slicer can be generated in two ways, depending on the signal coding scheme used. In case of a signal coding scheme without DC content such as Manchester coding the threshold can be generated using an external R-C integrator as shown in the following . The cut-off frequency of the R-C integrator has to be lower than the lowest frequency appearing in the data signal. In order to keep distortion low, the minimum value for R is  $20k\Omega$ .



Data slice1.wmf

Figure 4-5 Data Slicer Threshold Generation with External R-C Integrator

Another possibility for threshold generation is to use the peak detector in connection with two resistors and one capacitor as shown in the following figure. The component values are depending on the coding scheme and the protocol used.



Data\_slice2.wm

Figure 4-6 Data Slicer Threshold Generation Utilising the Peak Detector

5.5

# 5.1 Electrical Data. 5-2 5.2 Test Circuit 5-8 5.3 Test Board Layouts 5-9 5.4 Bill of Materials 5-11

Appendix - Noise Figure and Gain Circles . . . . . . . . . . . . . . 5-13

#### 5.1 Electrical Data

#### 5.1.1 Absolute Maximum Ratings



#### **WARNING**

The maximum ratings may not be exceeded under any circumstances, not even momentarily and individually, as permanent damage to the IC will result.

Tabl	Table 5-1 Absolute Maximum Ratings, Ambient temperature T <sub>AMB</sub> =-40°C + 85°C									
#	Parameter	Symbol	Limit Values		Unit	Remarks				
			min	max						
1	Supply Voltage	$V_s$	-0.3	5.5	V					
2	Junction Temperature	Tj	-40	+150	°C					
3	Storage Temperature	T <sub>s</sub>	-40	+125	°C					
4	Thermal Resistance	R <sub>thJA</sub>		114	K/W					
5	ESD integrity, all pins	V <sub>ESD</sub>	-1	+1	kV	HBM according to MIL STD 883D, method 3015.7				

#### 5.1.2 Operating Range

Within the operating range the IC operates as explained in the circuit description. The AC/DC characteristic limits are not guaranteed.

Supply voltage: VCC = 4.5V .. 5.5V

Та	Table 5-2 Operating Range, Ambient temperature T <sub>AMB</sub> = -40°C + 85°C									
#	Parameter	Symbol	Limit \	/alues	Unit	Test Conditions	L	Item		
			min	max						
1	Supply Current	I <sub>S</sub>		5.2	mA	f <sub>RF</sub> = 315MHz				
2	Receiver Input Level	RF <sub>in</sub>	-110	-13	dBm	$@$ source impedance $50\Omega$ , BER 2E-3, average power level, Manchester encoded datarate 4kBit, 280kHz IF Bandwidth	•			
3	LNI Input Frequency	f <sub>RF</sub>	310	350	MHz					
4	MI/X Input Frequency	f <sub>MI</sub>	310	350	MHz					
5	3dB IF Frequency Range	f <sub>IF -3dB</sub>	5	23	MHz					
6	Powerdown Mode On	PWDN <sub>ON</sub>	0	0.8	V					
7	Powerdown Mode Off	PWDN <sub>OFF</sub>	2	V <sub>S</sub>	V					
8	Gain Control Voltage, LNA high gain state	V <sub>THRES</sub>	2.8	V <sub>S</sub>	V					
9	Gain Control Voltage, LNA low gain state	V <sub>THRES</sub>	0	0.7V	V					

<sup>■</sup> This value is guaranteed by design.



#### 5.1.3 AC/DC Characteristics

AC/DC characteristics involve the spread of values guaranteed within the specified voltage and ambient temperature range. Typical characteristics are the median of the production. The device performance parameters marked with ■ were measured on an Infineon evaluation board as desdribed in Section 5.2

Tab	Table 5-3 AC/DC Characteristics with T <sub>A</sub> 25 °C, V <sub>VCC</sub> = 4.5 5.5 V								
#	Parameter	Symbol	L	imit Valu	ies	Unit	Test Conditions	L	Item
			min	typ	max				
Su	Supply								
Su	oply Current								
1	Supply current, standby mode	I <sub>S PDWN</sub>		50	70	nA	Pin 27 (PDWN) open or tied to 0 V		
2	Supply current	I <sub>S</sub>		4.6	5	mA			
LN	A								
Sig	nal Input LNI (PIN 3), V <sub>THR</sub>	<sub>ES</sub> > 2.8V, hi	gh gain	mode					
1	Average Power Level at BER = 2E-3 (Sensitivity)	RF <sub>in</sub>		-112		dBm	Manchester encoded datarate 4kBit, 280kHz IF Bandwidth	•	
2	Input impedance, f <sub>RF</sub> = 315 MHz	S <sub>11 LNA</sub>	0.8	395 / <b>-</b> 25.	5 deg			•	
3	Input level @ 1dB C.P. f <sub>RF</sub> =315 MHz	P1dB <sub>LNA</sub>		-14		dBm		•	
4	Input 3 <sup>rd</sup> order intercept point f <sub>RF</sub> = 315 MHz	IIP3 <sub>LNA</sub>		-10		dBm	f <sub>in</sub> = 315 & 317MHz	•	
5	LO signal feedthrough at antenna port	LO <sub>LNI</sub>		-119		dBm			
Sig	nal Output LNO (PIN 6), V <sub>TI</sub>	HRES > 2.8V,	high ga	in mode					
1	Gain f <sub>RF</sub> = 315 MHz	S <sub>21 LNA</sub>	1.5	77 / 150.	3 deg				
2	Output impedance, f <sub>RF</sub> = 315 MHz	S <sub>22 LNA</sub>	0.8	397 / -10.3	3 deg			•	
3	Voltage Gain Antenna to MI f <sub>RF</sub> = 315 MHz	G <sub>AntMI</sub>		21		dB			
4	Noise Figure	NF <sub>LNA</sub>		2		dB	excluding matching network loss - see Appendix	•	
Sig	nal Input LNI, V <sub>THRES</sub> = GN	ID, low gain	mode						
1	Input impedance, f <sub>RF</sub> = 315 MHz	S <sub>11 LNA</sub>	0.9	918 / -25.2	2 deg			•	
2	Input level @ 1dB C. P. f <sub>RF</sub> = 315 MHz	P1dB <sub>LNA</sub>		-7		dBm	matched input	•	



Tab	ole 5-3 AC/DC Characterist	ics with T <sub>A</sub> 2	25 °C, V <sub>V</sub>	<sub>CC</sub> = 4.5	5.5 V (c	ontinue	d)		
	Parameter	Symbol	L	imit Valu	ıes	Unit	Test Conditions	L	Item
			min	typ	max				
Sig	nal Input LNI, V <sub>THRES</sub> = GN	D, low gain	mode						
3	Input 3 <sup>rd</sup> order intercept point f <sub>RF</sub> = 315 MHz	IIP3 <sub>LNA</sub>		-13		dBm	f <sub>in</sub> = 315 & 317MHz	•	
Sig	nal Output LNO, V <sub>THRES</sub> =	GND, low ga	in mode	:					
1	Gain f <sub>RF</sub> = 315 MHz	S <sub>21 LNA</sub>	0.0	07 / 153.	7 deg				
2	Output impedance, f <sub>RF</sub> = 315 MHz	S <sub>22 LNA</sub>	0.9	907 / -10.	5 deg				
3	Voltage Gain Antenna to MI f <sub>RF</sub> = 315 MHz	G <sub>AntMI</sub>		2		dB			
Sig	nal 3VOUT (PIN 24)								
1	Output voltage	V <sub>3VOUT</sub>		3		V			
2	Current out	I <sub>3VOUT</sub>			50	μΑ			
Sig	nal THRES (PIN 23)								
1	Input Voltage range	V <sub>THRES</sub>	0		V <sub>S</sub> -1V	V	see chapter 4.1		
2	LNA low gain mode	V <sub>THRES</sub>	0			V			
3	LNA high gain mode	V <sub>THRES</sub>	2.8	3	V <sub>S</sub>	V	or shorted to Pin 24		
4	Current in	I <sub>THRES_in</sub>		5		nA			
Sig	nal TAGC (PIN 4)								
1	Current out, LNA low gain state	I <sub>TAGC_out</sub>		4.2		μA	RSSI > V <sub>THRES</sub>		
2	Current in, LNA high gain state	I <sub>TAGC_in</sub>		1.5		μA	RSSI < V <sub>THRES</sub>		
МІХ	(ER								
Sig	nal Input MI/MIX (PINS 8/9)								
1	Input impedance, f <sub>RF</sub> = 315 MHz	S <sub>11 MIX</sub>	0.9	954 / -10.9	9 deg				
2	Input 3 <sup>rd</sup> order intercept point	IIP3 <sub>MIX</sub>		-25		dBm			
Sig	nal Output IFO (PIN 12)								
1	Output impedance	Z <sub>IFO</sub>		330		Ω			
2	Conversion Voltage Gain f <sub>RF</sub> =869 MHz	G <sub>MIX</sub>		+21		dB			
3	Noise Figure, SSB (~DSB NF+3dB)	NF <sub>MIX</sub>		13		dB		•	
4	RF to IF isolation	A <sub>RF-IF</sub>		46		dB			



	Parameter	Symbol	L	₋imit Valu	ıes	Unit	Test Conditions	L	Item
			min	typ	max				
II.	IITER								
	nal Input LIM/X (PINS 17/18	)							
1	Input Impedance	Z <sub>LIM</sub>	264	330	396	Ω			
2	RSSI dynamic range	DR <sub>RSSI</sub>	60		80	dB			
3	RSSI linearity	LIN <sub>RSSI</sub>		±1		dB			
4	Operating frequency (3dB points)	f <sub>LIM</sub>	5	10.7	23	MHz		•	
DA <sup>·</sup>	TA FILTER								
1	Useable bandwidth	BW <sub>BB</sub> FILT			100	kHz		•	
2	RSSI Level at Data Filter Output SLP	RSSI <sub>low</sub>	0.9			V	LNA in high gain RF <sub>IN</sub> ~-103dBm		
3	RSSI Level at Data Filter Output SLP	RSSI <sub>high</sub>			2.8	V	LNA in high gain. RF <sub>IN</sub> ~-30dBm		
SLI	CER								
Sig	nal Output DATA (PIN 25)								
1	Useable bandwith	BW <sub>BB</sub> SLIC			100	kHz		•	
2	Capacitive loading of output	C <sub>max</sub> SLIC			20	pF			
3	LOW output voltage	V <sub>SLIC_L</sub>		0		V			
4	HIGH output voltage	V <sub>SLIC_H</sub>			V <sub>S</sub> -1V	V			
5	Output current	I <sub>SLIC_out</sub>			200	μA			
PE	AK DETECTOR								
Sig	nal Output PDO (PIN 26)								
1	LOW output voltage	V <sub>SLIC_L</sub>		0		V			
2	HIGH output voltage	V <sub>SLIC_H</sub>			V <sub>S</sub> -1	V			
3	Load current	I <sub>load</sub>			500	μΑ			
4	Leakage current	I <sub>leakage</sub>		700		nA			

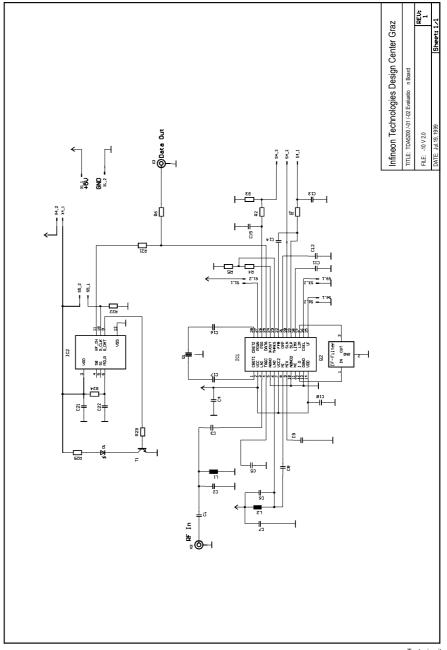


	Parameter	Symbol	ı	imit Valu	ies	Unit	Test Conditions	L	Item
		,	min	typ	max				
<b>~</b>	VOTAL 000U LATOR								
	YSTAL OSCILLATOR nais CRSTL1, CRISTL 2, (P	INC 1/20\							
oly 1	Operating frequency		5		11	MHz	fundamental mode,		
•	Operating frequency	<sup>f</sup> CRSTL	3		''	IVII IZ	series resonance		
2	Input Impedance	Z <sub>1-28</sub>		-760		Ω			
	@ ~5MHz			+j580					
3	Input Impedance @ ~10MHz	Z <sub>1-28</sub>		-600 +j870		Ω			
4	Serial Capacity	CC1		9.3		pF			
4	@ ~5MHz	C <sub>S 5</sub> =C1		9.3		рг			
5	Serial Capacity	C <sub>S10</sub> =C1		6.4		pF			
	@ ~10MHz	0.0				·			
PLI	<u>L</u>								
	nal LF (PIN 15)								
1	Tuning voltage relative to	V <sub>TUNE</sub>	0.4	1.6	2.4	V			
	V <sub>s</sub>	-							
РΟ	WER DOWN MODE								
Sig	nal PDWN (PIN 27)								
1	Powerdown Mode On	PWDNO	0		0.8	V			
_		N							
2	Powerdown Mode Off	PWDN <sub>Off</sub>	2.8		V <sub>S</sub>	V			
3	Input bias current PDWN	I <sub>PDWN</sub>		t.b.d.		μA			
4	Start-up Time until valid IF signal is detected	T <sub>SU</sub>			1	mS			
	oignario detected								
	L DIVIDER								
	nal CSEL (PIN 16)								
1	f <sub>CRSTL</sub> range 5.xxMHz	V <sub>CSEL</sub>	1.4		4	V	or open		
2	f <sub>CRSTL</sub> range 10.xxMHz	V <sub>CSEL</sub>	0		0.2	V			
3	Input bias current CSEL	I <sub>CSEL</sub>		5		μA	CSEL tied to GND		
-	,	OSEL		_		L., ,			

<sup>■</sup> Measured only in lab.

#### 5.2 Test Circuit

The device performance parameters marked with in Section 5.1.3 were measured on an Infineon evaluation board. This evaluation board can be obtained together with evaluation boards of the accompanying transmitter device TDA5101 in an evaluation kit that may be ordered on the INFINEON RKE Webpage www.infineon.com/rke



Test\_circuit.wmf

Figure 5-1 Schematic of the Evaluation Board



# 5.3 Test Board Layouts

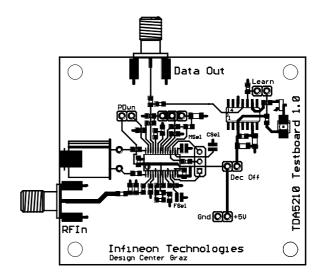


Figure 5-2 Top Side of the Evaluation Board

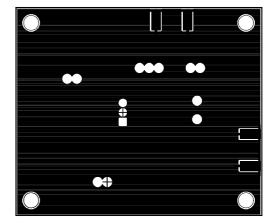


Figure 5-3 Bottom Side of the Evaluation Board

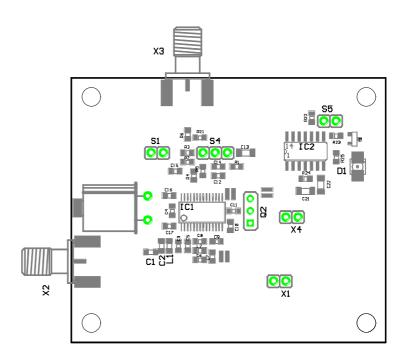


Figure 5-4 Component Placement on the Evaluation Board



#### 5.4 Bill of Materials

The following components are necessary for evaluation of the TDA5201 at 315MHz without use of a Microchip HCS515 decoder.

Table 5-4 Bill of	of Materials	
Ref	Value	Specification
R1	100kΩ	0805, ± 5%
R2	100kΩ	0805, ± 5%
R3	820kΩ	0805, ± 5%
R4	120kΩ	0805, ± 5%
R5	180kΩ	0805, ± 5%
R6	10kΩ	0805, ± 5%
L1	15nH	Toko, PTL2012-F15N0G
L2	12pF	0805,COG, ± 2%
C1	3.3 pF	0805, COG, ± 0.1pF
C2	10pF	0805, COG, ± 0.1pF
C3	6.8pF	0805, COG, ± 0.1pF
C4	100pF	0805, COG, ± 5%
C5	47nF	1206, X7R, ± 10%
C6	15nH	Toko, PTL2012-F15N0G
C7	100pF	0805, COG, ± 5%
C8	33pF	0805, COG, ± 5%
C9	100pF	0805, COG, ± 5%
C10	10nF	0805, X7R, ± 10%
C11	10nF	0805, X7R, ± 10%
C12	220pF	0805, COG, ± 5%
C13	47nF	0805, X7R, ± 10%
C14	470pF	0805, COG, ± 5%
C15	47nF	0805, X7R, ± 10%
C16	18pF	0805, COG, ± 0.1pF
C17	12pF	0805, COG, ± 2%
Q2	(315 + 10.7MHz)/32	HC49/U, fundamental mode, C <sub>L</sub> = 12pF,
F1	SFF10 7ΜΔ5-Δ	
-		
	142-0701-001	
	TDA 5201	
C8 C9 C10 C11 C12 C13 C14 C15 C16 C17	33pF 100pF 10nF 10nF 220pF 47nF 470pF 47nF 18pF 12pF	0805, COG, ± 5%  0805, COG, ± 5%  0805, X7R, ± 10%  0805, X7R, ± 10%  0805, COG, ± 5%  0805, X7R, ± 10%  0805, X7R, ± 10%  0805, COG, ± 5%  0805, COG, ± 5%  0805, COG, ± 0.1pF  0805, COG, ± 2%



The following components are necessary in addition to the above mentioned ones for evaluation of the TDA5201 in conjunction with a Microchip HCS515 decoder.

Table 5-5 Bill of	of Materials Addendum	
Ref	Value	Specification
R21	22kΩ	0805, ± 5%
R22	100kΩ	0805, ± 5%
R23	22kΩ	0805, ± 5%
R24	820kΩ	0805, ± 5%
R25	560kΩ	0805, ± 5%
C21	100nF	1206, X7R, ± 10%
C22	100nF	1206, X7R, ± 10%
IC2	HCS515	Microchip
T1	BC 847B	Infineon
D1	LS T670-JL	Infineon

### 5.5 Appendix - Noise Figure and Gain Circles

The following gain and noise figure circles were measured utilizing Microlab Stub Stretchers and a HP8514 network analyser. Maximum gain is shown at point 1 at 18.5 dB, minimum noise figure ist 1.9dB at point 2, step size of circles is 0.5dB.

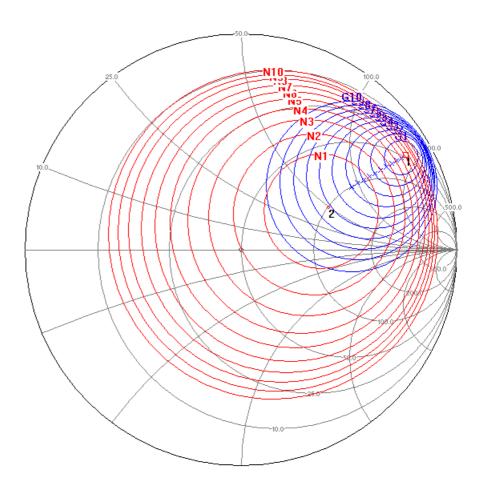


Figure 5-5 Gain and Noise Circles of the TDA5201 at 315 MHz.



#### **List of Figures**

# **List of Figures**

Figure 2-1	P-TSSOP-28-1 package outlines	2-3
igure 3-1	IC Pin Configuration	3-2
igure 3-2	Main Block Diagram	3-9
igure 4-1	LNA Automatic Gain Control Circuitry	4-2
igure 4-2	RSSI Level and Permissive AGC Threshold Levels	4-3
igure 4-3	Data Filter Design	4-4
igure 4-4	Determination of Series Capacitance Value for the Quartz Oscillator	4-5
igure 4-5	Data Slicer Threshold Generation with External R-C Integrator	4-7
igure 4-6	Data Slicer Threshold Generation Utilising the Peak Detector	4-7
igure 5-1	Schematic of the Evaluation Board	5-8
igure 5-2	Top Side of the Evaluation Board	5-9
igure 5-3	Bottom Side of the Evaluation Board	5-9
igure 5-4	Component Placement on the Evaluation Board	5-10
igure 5-5	Gain and Noise Circles of the TDA5201 at 315 MHz	5-13



#### **List of Tables**

# **List of Tables**

Table 3-1	Pin Definition and Function	3-3
Table 3-3	PDWN Pin Operating States	3-12
Table 5-1	Absolute Maximum Ratings, Ambient temperature T <sub>AMB</sub> =-40°C + 85°C	5-2
Table 5-2	Operating Range, Ambient temperature T <sub>AMB</sub> = -40°C + 85°C	5-3
Table 5-3	AC/DC Characteristics with TA 25 °C, VVCC = 4.5 5.5 V	5-4
Table 5-4	Bill of Materials	5-11
Table 5-5	Bill of Materials Addendum	5-12





**List of Tables**